

Features

- Uses CRM(CQ) advanced SkyMOS1 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

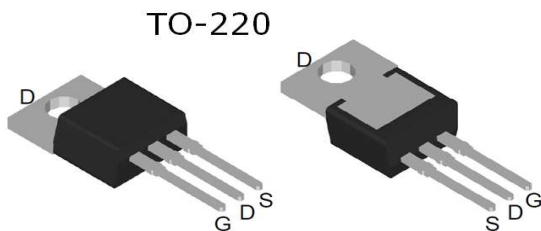
Product Summary

| | |
|------------------|------|
| V_{DS} | 100V |
| $R_{DS(on)}$ typ | 3mΩ |
| I_D | 120A |

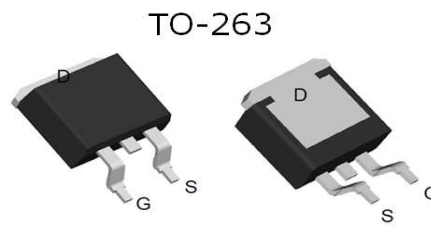
Applications

- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

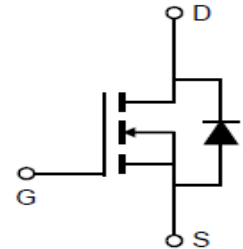
100% Avalanche Tested



CRST037N10N



CRSS035N10N



Package Marking and Ordering Information

| Part # | Marking | Package | Packing | Reel Size | Tape Width | Qty |
|-------------|---------|---------|---------|-----------|------------|-------|
| CRST037N10N | - | TO-220 | Tube | N/A | N/A | 50pcs |
| CRSS035N10N | - | TO-263 | Tube | N/A | N/A | 50pcs |

Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|----------------|-------------------|------------------|
| Drain-source voltage | V_{DS} | 100 | V |
| Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit) | I_D | 190 120 120 | A |
| Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax}) | $I_{D\ pulse}$ | 480 | A |
| Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$) | E_{AS} | 410 | mJ |
| Gate-Source voltage | V_{GS} | ± 20 | V |
| Power dissipation ($T_C = 25^\circ\text{C}$) | P_{tot} | 227 | W |
| Operating junction and storage temperature | T_j, T_{stg} | -55...+150 | $^\circ\text{C}$ |

Thermal Resistance

| Parameter | Symbol | Max | Unit |
|--|------------|------|------|
| Thermal resistance, junction – case. | R_{thJC} | 0.55 | °C/W |
| Thermal resistance, junction – ambient(min. footprint) | R_{thJA} | 62 | |

Electrical Characteristic (at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified)

| Parameter | Symbol | Value | | | Unit | Test Condition |
|-----------|--------|-------|------|------|------|----------------|
| | | min. | typ. | max. | | |

Static Characteristic

| | | | | | | |
|----------------------------------|--------------|-----|------|-----|---------|---|
| Drain-source breakdown voltage | BV_{DSS} | 100 | - | - | V | $V_{GS}=0V, I_D=250\mu A$ |
| Gate threshold voltage | $V_{GS(th)}$ | 2 | 3 | 4 | V | $V_{DS}=V_{GS}, I_D=250\mu A$ |
| Zero gate voltage drain current | I_{DSS} | - | 0.05 | 1 | μA | $V_{DS}=100V, V_{GS}=0V$ $T_j=25^\circ C$ $T_j=125^\circ C$ |
| Gate-source leakage current | I_{GSS} | - | 10 | 100 | nA | $V_{GS}=\pm 20V, V_{DS}=0V$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 3.0 | 3.7 | mΩ | $V_{GS}=10V, I_D=50A,$ TO-220 TO-263 |
| Transconductance | g_{fs} | - | 108 | - | S | $V_{DS}=5V, I_D=50A$ |

Dynamic Characteristic

| | | | | | | |
|------------------------------|--------------|---|------|---|----|--|
| Input Capacitance | C_{iss} | - | 9538 | - | pF | $V_{GS}=0V, V_{DS}=50V,$ $f=1MHz$ |
| Output Capacitance | C_{oss} | - | 1154 | - | | |
| Reverse Transfer Capacitance | C_{rss} | - | 36 | - | | |
| Gate Total Charge | Q_G | - | 139 | - | nC | $V_{GS}=10V, V_{DS}=50V,$ $I_D=20A, f=1MHz$ |
| Gate-Source charge | Q_{gs} | - | 46 | - | | |
| Gate-Drain charge | Q_{gd} | - | 28 | - | | |
| Turn-on delay time | $t_{d(on)}$ | - | 28 | - | ns | $V_{GS}=10V, V_{DS}=50V,$ $R_G=2.5\Omega$ |
| Rise time | t_r | - | 37 | - | | |
| Turn-off delay time | $t_{d(off)}$ | - | 81 | - | | |
| Fall time | t_f | - | 51 | - | | |
| Gate resistance | R_G | - | 1.9 | - | Ω | $V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$ |

Body Diode Characteristic

| Parameter | Symbol | Value | | | Unit | Test Condition |
|------------------------------------|----------|-------|------|------|------|----------------------------------|
| | | min. | typ. | max. | | |
| Body Diode Forward Voltage | V_{SD} | - | 0.78 | 1.2 | V | $V_{GS}=0V, I_{SD}=50A$ |
| Body Diode Reverse Recovery Time | t_{rr} | - | 55 | - | ns | $I_F=20A,$ $dI/dt=500A/\mu s$ |
| Body Diode Reverse Recovery Charge | Q_{rr} | - | 460 | - | nC | |

Typical Performance Characteristics

Fig 1: Output Characteristics

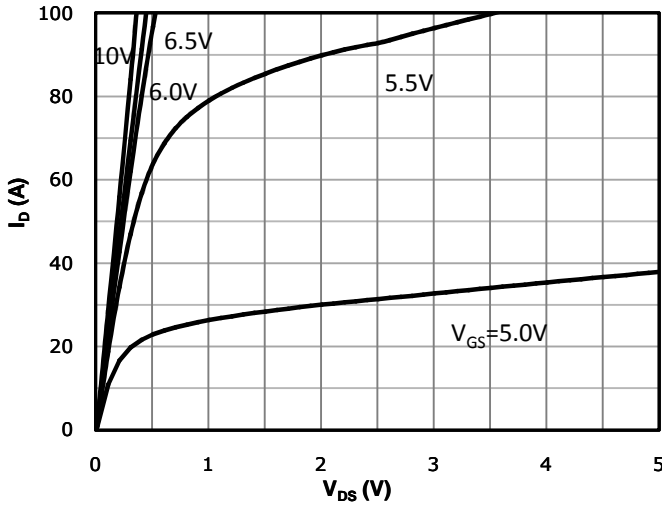


Fig 2: Transfer Characteristics

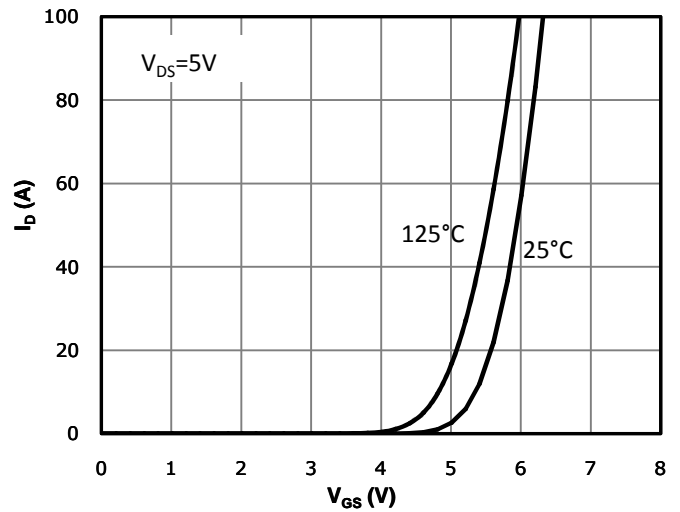


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

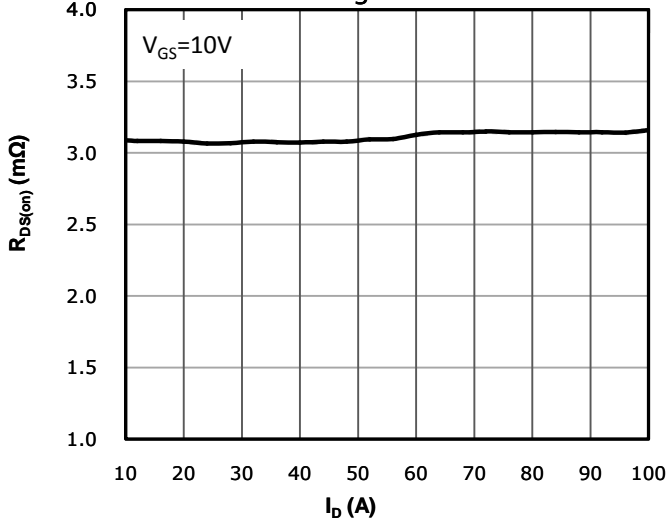


Fig 4: $R_{DS(on)}$ vs Gate Voltage

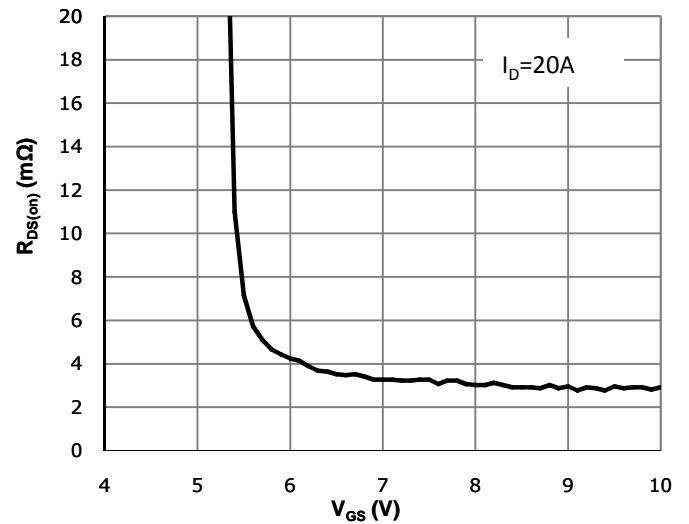


Fig 5: $R_{DS(on)}$ vs. Temperature

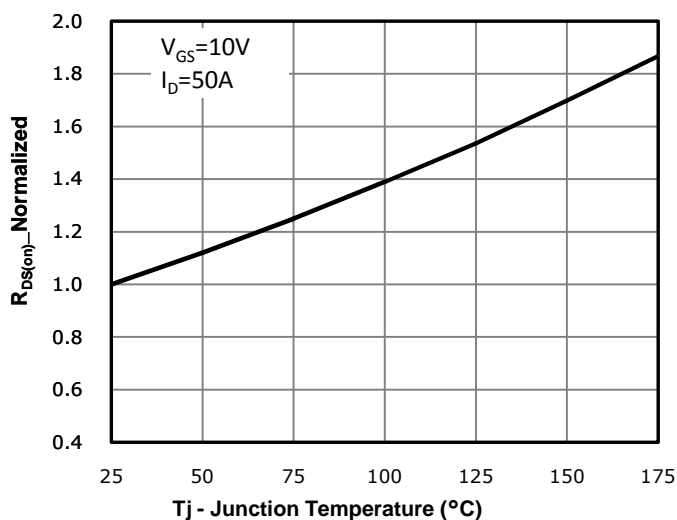


Fig 6: Capacitance Characteristics

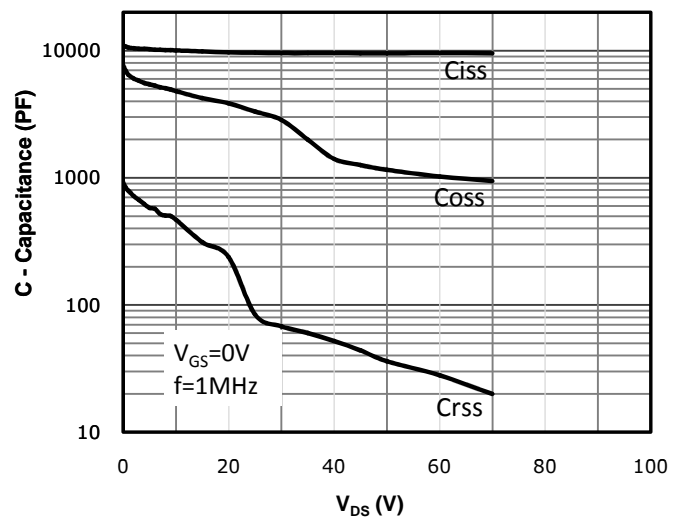


Fig 7: Gate Charge Characteristics

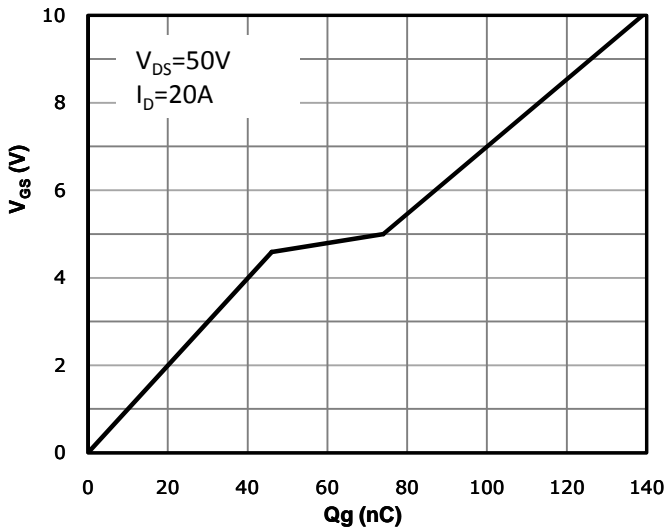


Fig 8: Body-diode Forward Characteristics

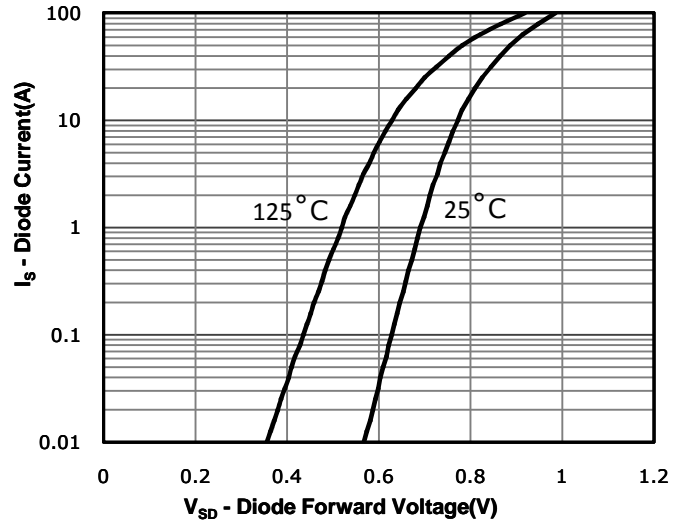


Fig 9: Power Dissipation

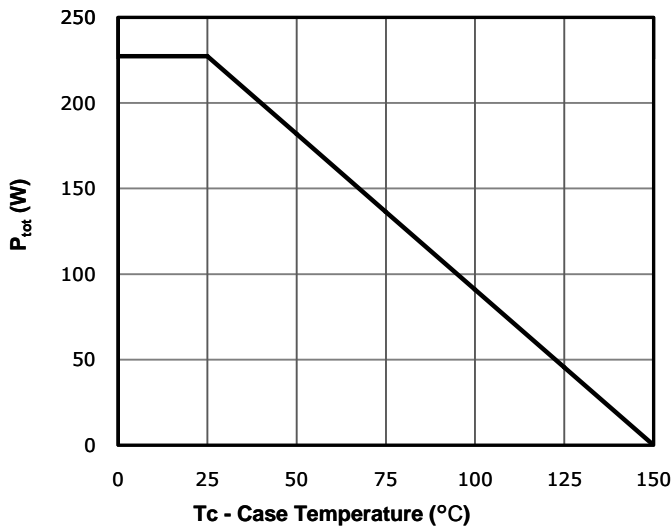


Fig 10: Drain Current Derating

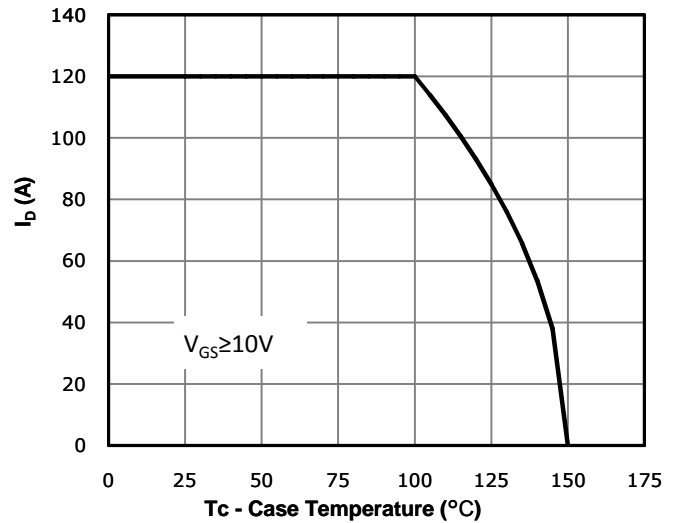


Fig 11: Safe Operating Area

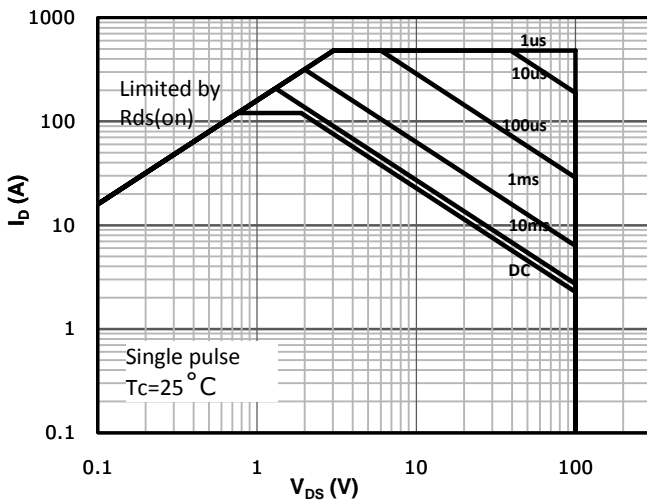
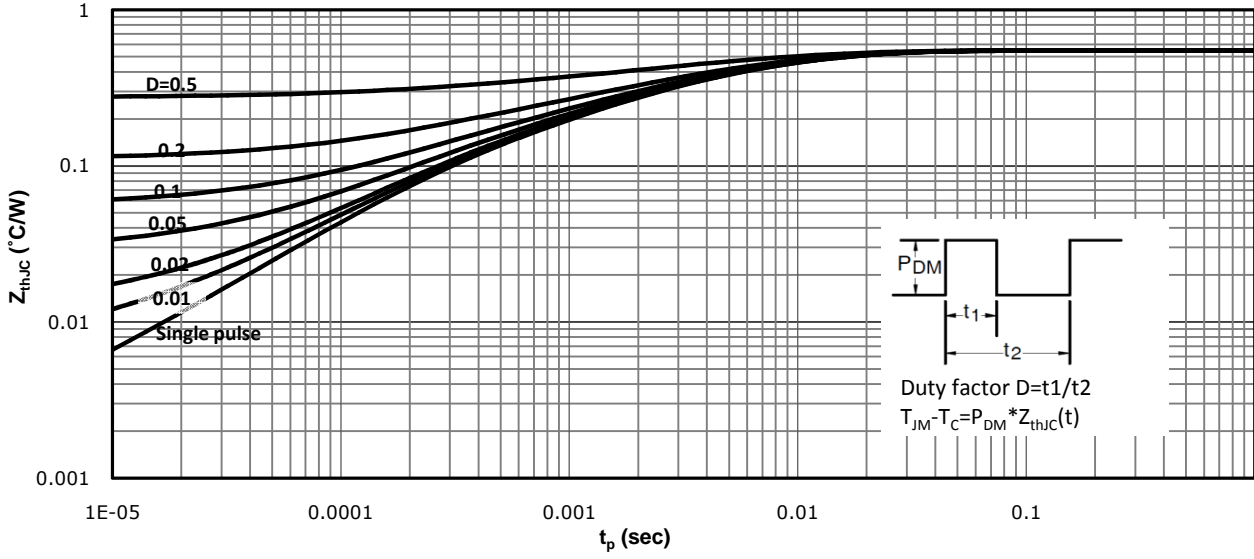
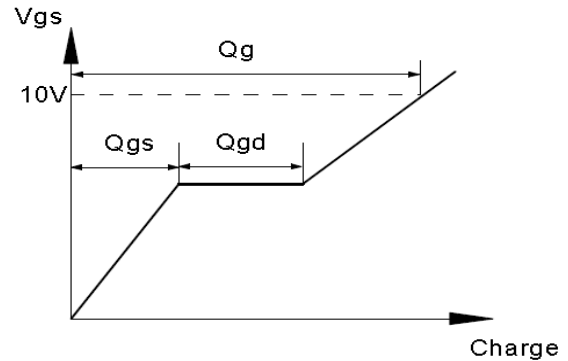
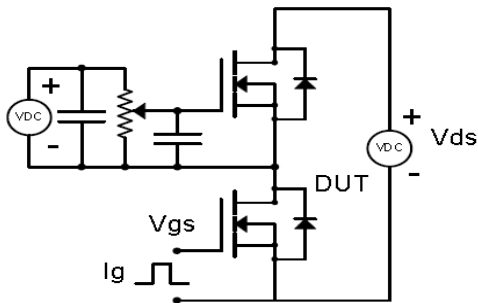


Fig 12: Max. Transient Thermal Impedance

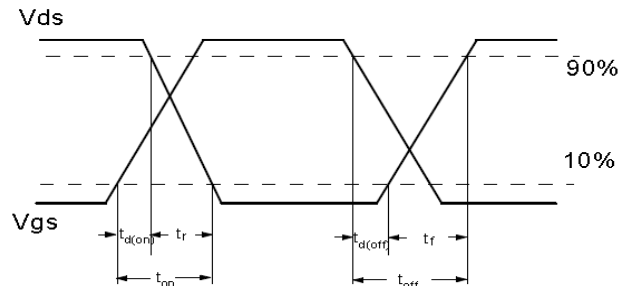
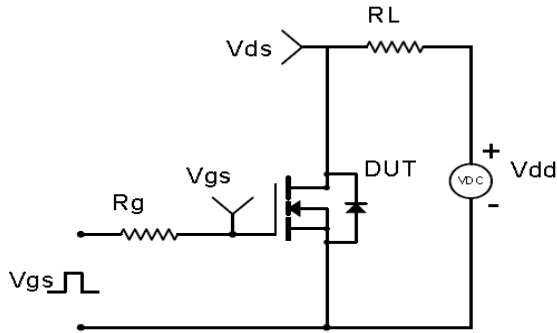


Test Circuit & Waveform

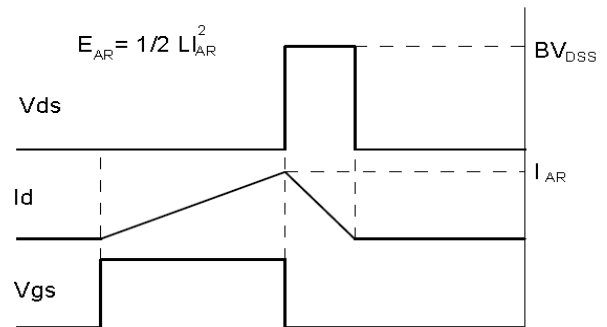
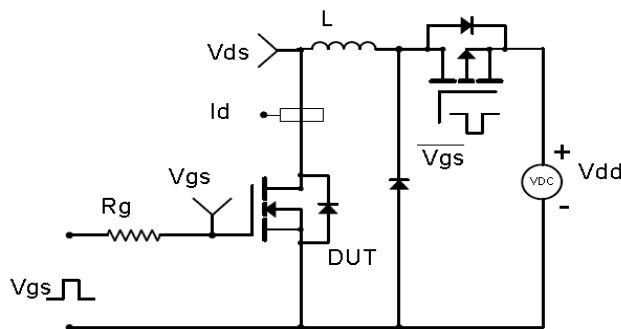
Gate Charge Test Circuit & Waveform



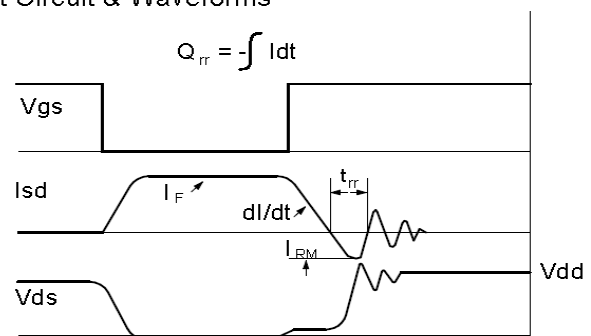
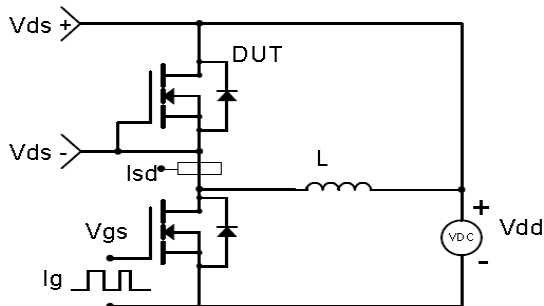
Resistive Switching Test Circuit & Waveforms



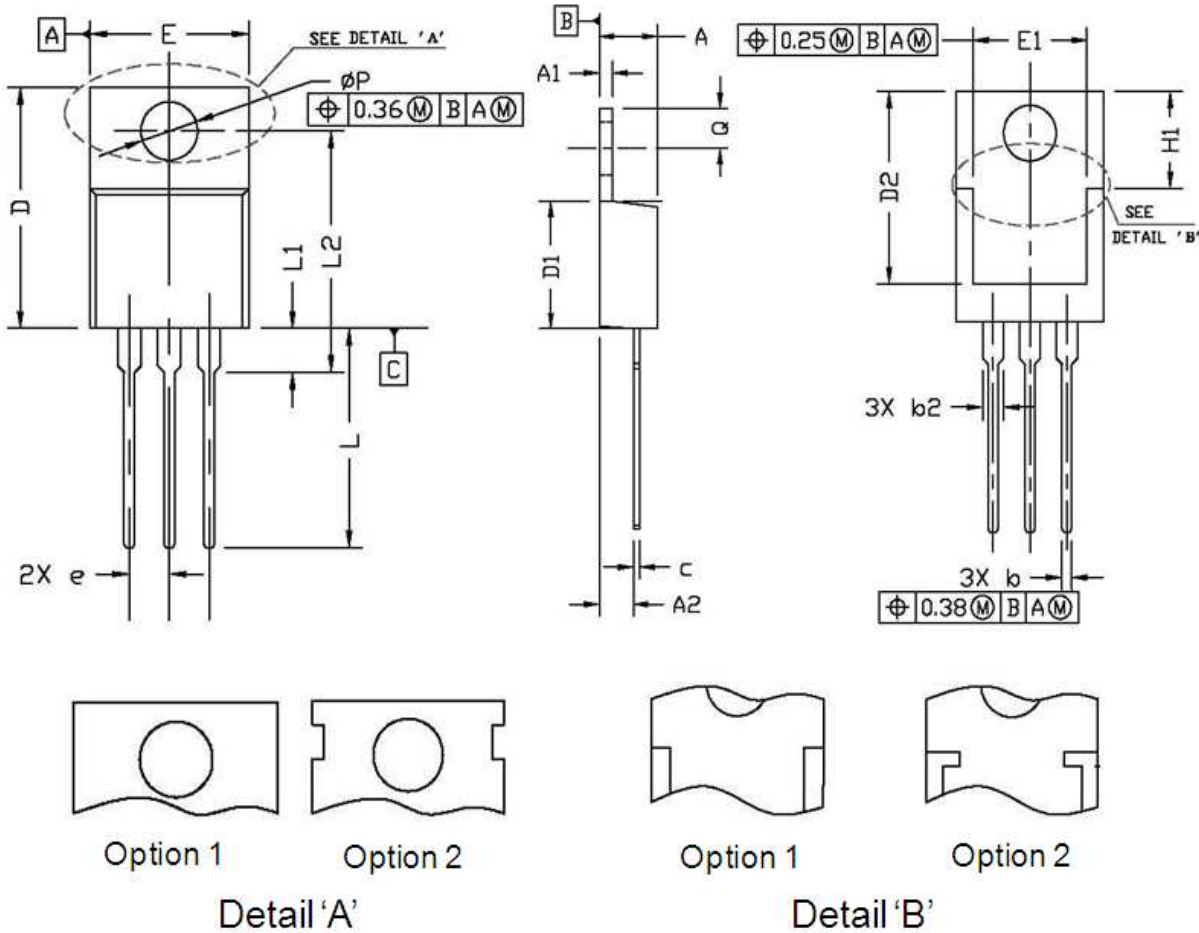
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

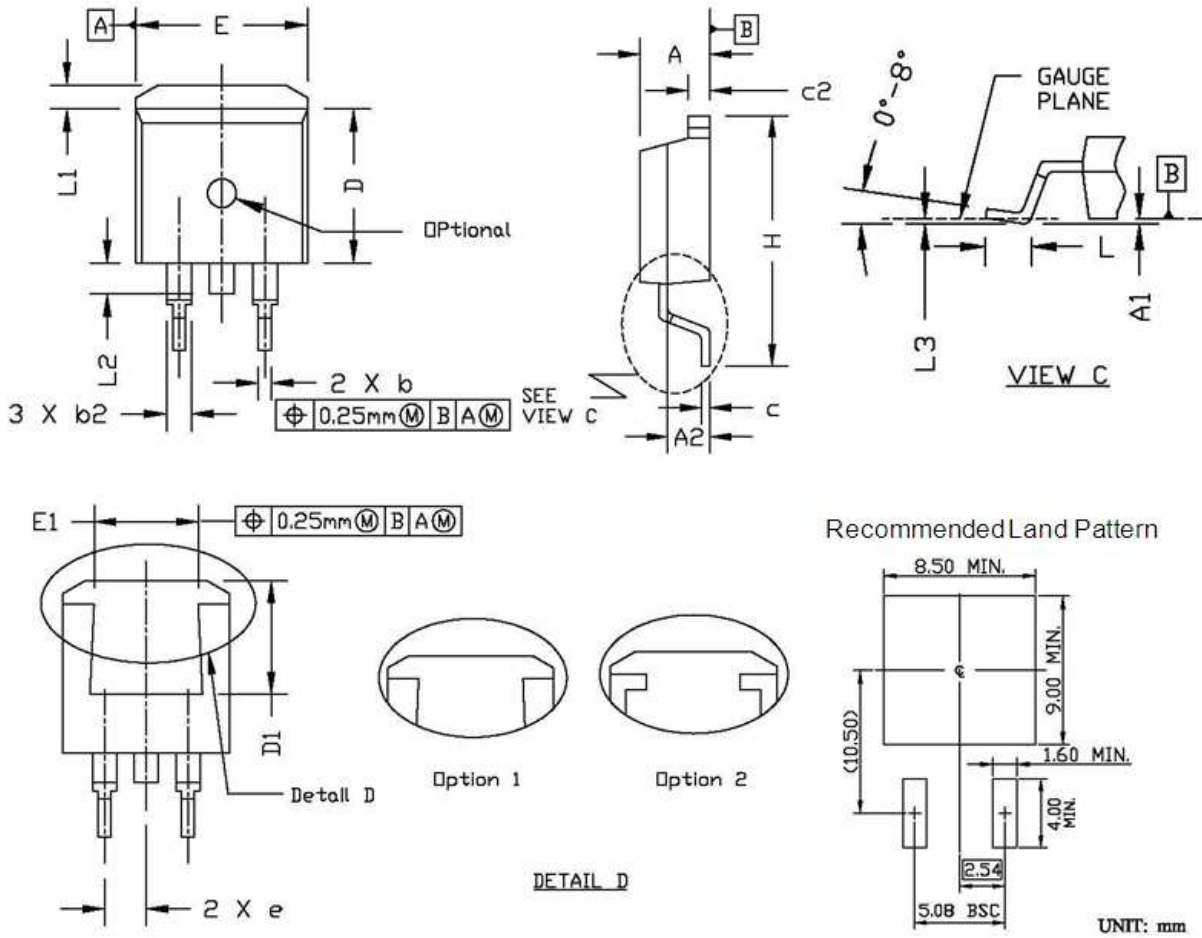


Package Outline: TO-220-3L



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.30 | 4.80 | 0.169 | 0.189 |
| A1 | 1.20 | 1.45 | 0.047 | 0.057 |
| A2 | 2.20 | 2.90 | 0.087 | 0.114 |
| b | 0.69 | 0.95 | 0.027 | 0.037 |
| b2 | 1.00 | 1.60 | 0.039 | 0.063 |
| c | 0.33 | 0.65 | 0.013 | 0.026 |
| D | 14.70 | 16.20 | 0.579 | 0.638 |
| D1 | 8.59 | 9.65 | 0.338 | 0.380 |
| D2 | 11.75 | 13.60 | 0.463 | 0.535 |
| e | 2.54 BSC. | | 0.100 BSC. | |
| E | 9.60 | 10.60 | 0.378 | 0.417 |
| E1 | 7.00 | 8.46 | 0.276 | 0.333 |
| H1 | 6.20 | 7.00 | 0.244 | 0.276 |
| L | 12.60 | 14.80 | 0.496 | 0.583 |
| L1 | 2.70 | 3.80 | 0.106 | 0.150 |
| L2 | 12.13 | 16.50 | 0.478 | 0.650 |
| Q | 2.40 | 3.10 | 0.094 | 0.122 |
| P | 3.50 | 3.90 | 0.138 | 0.154 |

Package Outline: TO-263



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.30 | 4.86 | 0.169 | 0.191 |
| A1 | 0.00 | 0.25 | 0.000 | 0.010 |
| A2 | 2.34 | 2.79 | 0.092 | 0.110 |
| b | 0.68 | 0.94 | 0.027 | 0.037 |
| b2 | 1.15 | 1.35 | 0.045 | 0.053 |
| c | 0.33 | 0.65 | 0.013 | 0.026 |
| c2 | 1.17 | 1.40 | 0.046 | 0.055 |
| D | 8.38 | 9.45 | 0.330 | 0.372 |
| D1 | 6.90 | 8.17 | 0.272 | 0.322 |
| e | 2.54 BSC. | | 0.100 BSC. | |
| E | 9.78 | 10.50 | 0.385 | 0.413 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| H | 14.61 | 15.88 | 0.575 | 0.625 |
| L | 2.24 | 3.00 | 0.088 | 0.118 |
| L1 | 0.70 | 1.60 | 0.028 | 0.063 |
| L2 | 1.00 | 1.78 | 0.039 | 0.070 |
| L3 | 0.00 | 0.25 | 0.000 | 0.010 |

Revision History

| Revision | Date | Major changes |
|----------|------------|----------------------------------|
| 1.0 | 2018-02-09 | Release of formal version. |
| 2.0 | 2019-05-28 | Supplement package outline info. |

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

单击下面可查看定价，库存，交付和生命周期等信息

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